16-Channel Serial to Parallel Converter with High Voltage Backplane Driver and Push-Pull Outputs

Features

- ► HVCMOS® technology
- Output voltage up to +200V
- ► Shift register speed 500kHz @ V_{DD} = 1.7V
- 16 high voltage outputs
- High voltage backplane driver
- ► CMOS input levels

Applications

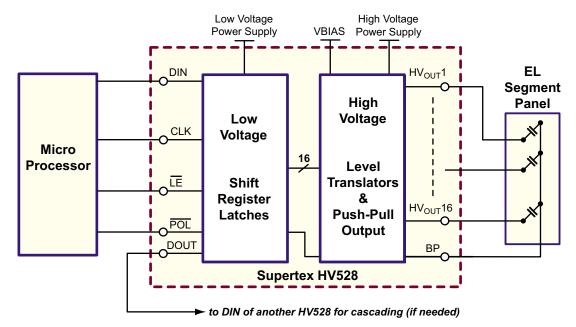
- Multiple segment EL display
- Piezoelectric transducer driver
- Braille driver

General Description

The HV528 is a 200V, 16-channel serial to parallel converter. The high voltage outputs and the backplane driver are designed to source and sink ±1.0mA.

The high voltage outputs are controlled by a 16-bit serial shift register, followed by a 16-bit latch. Data is shifted through the shift registers during the low to high clock transition. A data output buffer is provided for cascading multiple devices. Data is transferred to the 16-bit latch when a logic level low is applied to the LE input. Data is stored in the latch when LE is high. Output states are controlled by the data in the latch and by the POL pin.

Typical Application Circuit



Ordering Information

	Package Option
Device	32-Lead QFN 5.00x5.00mm body 1.00mm height (max) 0.50mm pitch
HV528	HV528K6-G

-G indicates package is RoHS compliant ('Green')



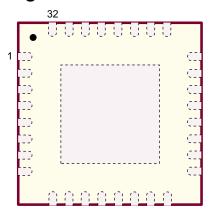


Absolute Maximum Ratings

Parameter	Value
Logic supply, V _{DD}	-0.5V to 7.0V
High voltage supply, V _{PP}	215V
Translator supply voltage, V _{BIAS}	-0.5V to 7.0V
Logic input levels	-0.5V to V _{DD} +0.5V
Operating junction temperature	-40°C to +125°C
Storage temperature range	-65°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



32-Lead QFN (K6) (top view) (Bottom side exposed center pad is at V_{pp} potential)

Product Marking



L = Lot Number
YY = Year Sealed
WW = Week Sealed
A = Assembler ID
C = Country of Origin
____ = "Green" Packaging

32-Lead QFN (K6)

Operating Supply Voltages and Conditions

Sym	Parameter	Min	Тур	Max	Units	Conditions
V _{DD}	Logic supply voltage	1.7	3.0	5.5	V	
V _{BIAS}	Level translator supply voltage	5.4	-	6.6	V	
V _{PP}	Positive high voltage supply	50	-	200	V	
V _{IH}	High-level input voltage	0.9V _{DD}	-	V _{DD}	V	
V _{IL}	Low-level input voltage	0	-		V	
T _A	Operating temperature	0	-	+70	°C	

Notes:

1. External ground noise reduction circuit will be provided by design upon characterization.

Power-up sequence should be the following*:

- 1. Apply ground
- 2. Apply V_{DD}
- 3. Set all inputs $(D_{IN}, CLK, \overline{LE}, \overline{POL})$ to a known state
- 4. Apply V_{BIAS}
- 5. Apply V_{pp}

Power-down sequence should be the reverse of the above

* This power up sequence requires an external high voltage diode between V_{DD} and V_{PP} Without the diode, power up V_{PP} to a V_{DD} level first to bias the silicon substrate. After all other signals are powered, finish raising the V_{PP} to its final level.

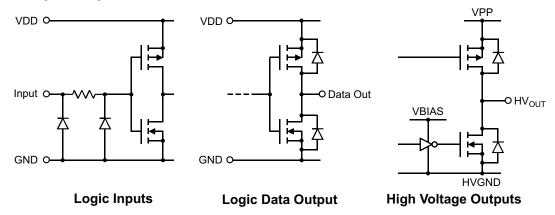
DC Electrical Characteristics (Over operating supply voltages and temperature, unless otherwise noted)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
I _{DD}	V _{DD} supply current	-	-	1.0	mA	f _{CLK} = 500kHz	
I _{DDQ}	Quiescent V _{DD} sup	ply current	-	-	10	μA	All logic inputs = V _{DD} or 0V
I _{BIAS}	V _{BIAS} supply curren	-	-	100	μA	All HV _{OUTS} switching at 1.0kHz. Peak I _{BIAS} = 200mA with all channels switching	
I _{BIASQ}	Quiescent V _{BIAS} cu	-	-	10	μA	No HV _{OUT} switching	
I _{PPQ}	Quiescent V _{PP} supply current		-	-	100	μA	V _{PP} = 200V, outputs are static
I _{IH}	High-level logic input current		-	-	10	μA	$V_{IH} = V_{DD}$
I _{IL}	Low-level logic inp	ut current	-	-	-10	μA	V _{IL} = 0V
		LIV & DD	V _{PP} -30V	-	-	V	IHV _{OUT} = -1.0mA, 50V ≤ V _{PP} ≤ 100V
V _{OH}	High level output	HV _{OUT} & BP	V _{PP} -16V	-	-	V	IHV _{OUT} = -1.0mA, 100V < V _{PP} ≤ 200V
		D _{out}	V _{DD} -1.0V	-	-	V	ID _{OUT} = -1.0mA
W	HV _{OUT} & BP		-	-	6.0	V	IHV _{OUT} = 1.0mA
V _{OL}	V _{oL} Low level output	D _{OUT}	-	-	1.0	V	ID _{OUT} = 1.0mA
C _{DIN}	Logic input capacit	-	-	10	pF		
C _{DOUT}	Logic output capac	citance	-	-	10	pF	

AC Electrical Characteristics (Over operating supply voltages and temperature, unless otherwise noted)

Sym	Parameter	Min	Тур	Max	Units	Conditions
f _{CLK}	Clock frequency	0	-	500	kHz	
t _c	Clock high / low pulse width	1.0	-	-	μs	
t _{su}	Data setup time before clock rises	50	-	-	ns	
t _H	Data hold time after clock rises	50	-	-	ns	
t _{CLE}	LE from CLK setup time	15	-	-	ns	
t _{wle}	LE pulse width	100	-	-	ns	
t _{DD}	Clock negative edge to D _{OUT} delay	-	-	150	ns	C_{LDOUT} = 50pF, (C_{LDOUT} includes C_{DIN} and C_{DOUT})
t _{PHV}	Delay time from inputs for HV _{OUT} / BP to start rise/fall	-	-	500	ns	V _{PP} = 200V, V _{BIAS} = 5.4V
t _{OR}	HV _{OUTPUT} / BP rise time	-	-	300	μs	$C_L = 1500 pF, V_{pp} = 200 V$
t _{OF}	HV _{OUTPUT} / BP fall time	-	-	300	μs	$C_L = 1500 pF, V_{BIAS} = 5.4 V, V_{PP} = 200 V$
t _{oc}	Width of POL pulses	$t_{PHV} + t_{OR}/t_{OF}$	-	-	μs	

Input and Output Equivalent Circuits

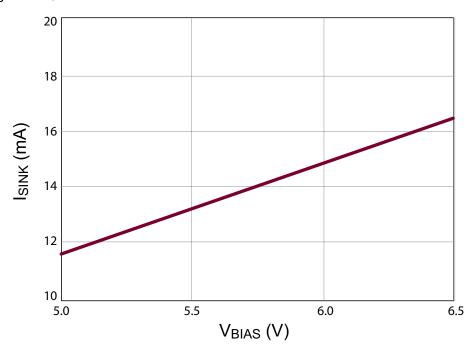


V_{BIAS} SUPPLY

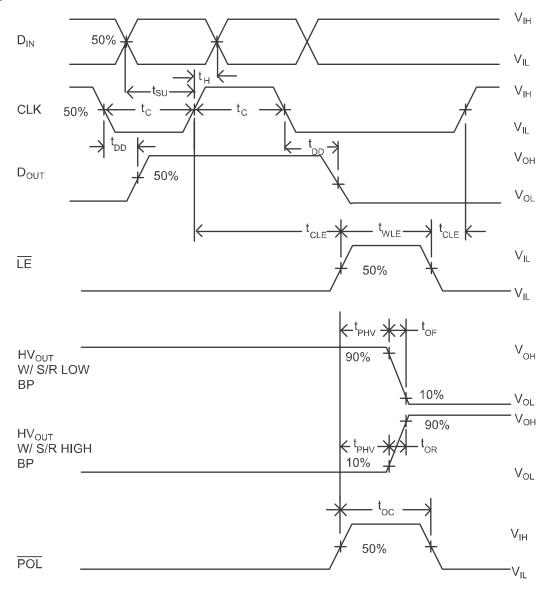
The $V_{\rm BIAS}$ supply operates from 5.4 to 6.6V. It is the gate drive voltage for all of the output N-channel MOSFETs. This allows the output peak current sink to be set by varying the $V_{\rm BIAS}$ voltage. A higher $V_{\rm BIAS}$ voltage will increase the current sinking capability.

The operating $\rm V_{DD}$ range is 1.7 to 5.5V. A plot showing the typical characteristics of $\rm I_{SINK}$ vs $\rm V_{BIAS}$ is shown below.

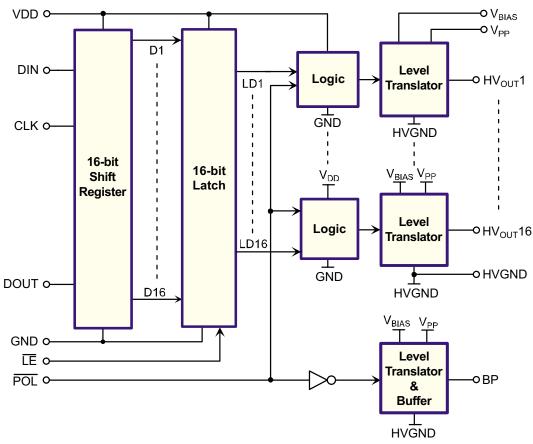
Typical HV_{OUT} I_{SINK} vs V_{BIAS} ($V_{PP} = 200V, C_{IOAD} = 1.0nF$)



Switching Waveforms



Functional Block Diagram



Function Table

		Inp	uts		Outputs						
Function	DIN	CLK	LE	POL	Shift Reg 1 216			DOUT			
Load S/R	H OR L	1	Н	Х	HorL ••	• ••	Х	•			
Transfer data in latch	Х	L	L	Н	* **	* **	L	•			
	Х	L	L	L	* **	* ** (b)	Н	•			
	Х	Х	Н	Н	• ••	• ••	L	•			
Store data in latches	Х	Х	Н	L	• ••	• •• (b)	Н	•			
Transparent made	L	1	L	Н	L ••	L ••	L	•			
Transparent mode	Н	↑	L	Н	Н ••	Н ••	L	•			
Invert mode	Х	X	Н	L	• ••	• •• (b)	Н	X			
	Х	Х	Н	Н	• ••	• ••	L	Х			

Notes:

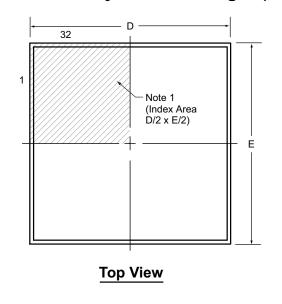
- H = high level, L = low level, X = irrelevant, ↑ = low-to-high transition_
- = dependent on previous stage's state before the last CLK or last LE low
- * = data at the last CLK ↑
- (b) = bar over all symbols

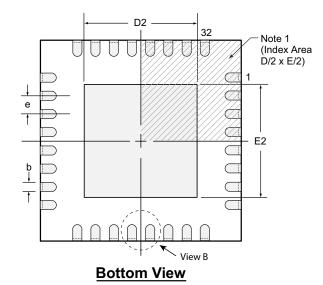
Pin Description

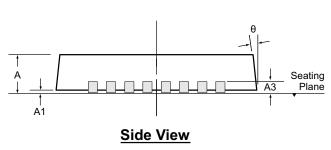
Pin #	Function	Description								
1	HV _{оυт} 12									
2	HV _{out} 11									
3	HV _{out} 10									
4	HV _{OUT} 9	Jigh voltago nuch null outnut								
5	HV _{OUT} 8									
6	HV _{out} 7									
7	HV _{out} 6	High voltage push-pull output								
8	HV _{OUT} 5									
9	HV _{out} 4									
10	HV _{OUT} 3									
11	HV _{OUT} 2									
12	HV _{out} 1									
13	NC	No connect								
14	VPP	High voltage supply								
15	GND	Logic ground								
16	NC	No connect								
17	DIN	Data in								
18	NC	No connect								
19	CLK	Clock input logic								
20	VDD	Logic supply voltage								
21	POL	Polarity bar input logic								
22	ĪĒ	Latch enable bar input logic								
23	NC	No connect								
24	DOUT	Data out								
25	NC	No connect								
26	VBIAS	Level translator bias voltage								
27	HVGND	High voltage ground								
28	BP	High voltage backplane output								
29	HV _{ουτ} 16									
30	HV _{ουτ} 15	High voltage push pull output								
31	HV _{OUT} 14	High voltage push-pull output								
32	HV _{ουτ} 13									
Center Pad		The center pad is at VPP potential. Leave floating or connect to VPP. Do not ground.								

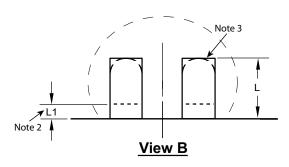
32-Lead QFN Package Outline (K6)

5.00x5.00mm body, 1.00mm height (max), 0.50mm pitch









Notes:

- A Pin 1 identifier must be located in the index area indicated. The Pin 1 Identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.
- Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.
- 3. The inner tip of the lead may be either rounded or square.

Symbo	ol	Α	A1	А3	b	D	D2	E	E2	е	L	L1	θ
	MIN	0.80	0.00		0.18	4.85*	1.05	4.85*	1.05		0.30 [†]	0.00	0 º
Dimension (mm)	NOM	0.90	0.02	0.20 REF	0.25	5.00	-	5.00	-	0.50 BSC	0.40 [†]	-	-
(mm)	MAX	1.00	0.05		0.30	5.15*	3.55 [†]	5.15*	3.55 [†]	200	0.50 [†]	0.15	14º

JEDEC Registration MO-220, Variation VHHD-6, Issue K, June 2006.

Drawings not to scale.

Supertex Doc. #: DSPD-32QFNK65X5P050, Version B090808.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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^{*} This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

[†] This dimension is a non-JEDEC dimension.